

## XPT IGBT

preliminary

$$V_{CES} = 1200V$$

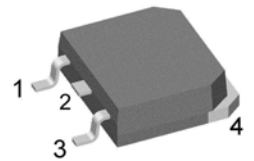
$$I_{C25} = 20A$$

$$V_{CE(sat)} = 1.8V$$

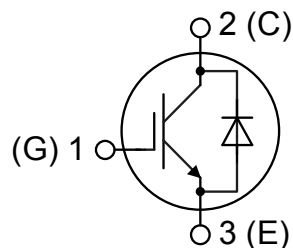
Copack

Part number

IXA12IF1200TC



Backside: collector

**Features / Advantages:**

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
  - short circuit rated for 10  $\mu$ sec.
  - very low gate charge
  - low EMI
  - square RBSOA @ 3x Ic
- Thin wafer technology combined with the XPT design results in a competitive low VCE(sat)
- SONIC™ diode
  - fast and soft reverse recovery
  - low operating forward voltage

**Applications:**

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

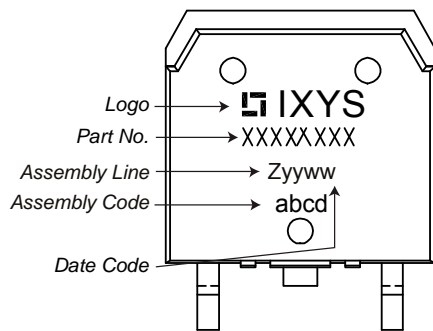
**Package:** TO-268AA (D3Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

IGBT				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{CES}$	collector emitter voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
$V_{GES}$	max. DC gate voltage				$\pm 20$	V	
$V_{GEM}$	max. transient gate emitter voltage				$\pm 30$	V	
$I_{C25}$	collector current	$T_C = 25^{\circ}C$			20	A	
$I_{C100}$		$T_C = 100^{\circ}C$			13	A	
$P_{tot}$	total power dissipation	$T_C = 25^{\circ}C$			85	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 10A; V_{GE} = 15V$		1.8	2.1	V	
				2.1		V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.3mA; V_{CE} = V_{CE}$	5.4	5.9	6.5	V	
$I_{CES}$	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0V$			0.1	mA	
				0.1		mA	
$I_{GES}$	gate emitter leakage current	$V_{GE} = \pm 20V$			500	nA	
$Q_{G(on)}$	total gate charge	$V_{CE} = 600V; V_{GE} = 15V; I_C = 10A$		27		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600V; I_C = 10A$ $V_{GE} = \pm 15V; R_G = 100\Omega$		70		ns	
$t_r$	current rise time		$T_{VJ} = 125^{\circ}C$		40		ns
$t_{d(off)}$	turn-off delay time				250		ns
$t_f$	current fall time				100		ns
$E_{on}$	turn-on energy per pulse				1.1		mJ
$E_{off}$	turn-off energy per pulse				1.1		mJ
<b>RBSOA</b>	reverse bias safe operating area	$V_{GE} = \pm 15V; R_G = 100\Omega$					
$I_{CM}$		$V_{CEmax} = 1200V$			30	A	
<b>SCSOA</b>	short circuit safe operating area	$V_{CEmax} = 900V$					
$t_{sc}$	short circuit duration	$V_{CE} = 900V; V_{GE} = \pm 15V$			10	$\mu s$	
$I_{sc}$	short circuit current	$R_G = 100\Omega; \text{non-repetitive}$		40		A	
$R_{thJC}$	thermal resistance junction to case				1.5	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.15		K/W	
<b>Diode</b>							
$V_{RRM}$	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
$I_{F25}$	forward current	$T_C = 25^{\circ}C$			22	A	
$I_{F100}$		$T_C = 100^{\circ}C$			14	A	
$V_F$	forward voltage	$I_F = 10A$			2.20	V	
				1.95		V	
$I_R$	reverse current	$V_R = V_{RRM}$			*	mA	
	* not applicable, see Ices value above				*	mA	
$Q_{rr}$	reverse recovery charge	$V_R = 600V$ $-di_F/dt = -250A/\mu s$ $I_F = 10A; V_{GE} = 0V$		1.3		$\mu C$	
$I_{RM}$	max. reverse recovery current		$T_{VJ} = 125^{\circ}C$		10.5		A
$t_{rr}$	reverse recovery time				350		ns
$E_{rec}$	reverse recovery energy				0.35		mJ
$R_{thJC}$	thermal resistance junction to case				1.8	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.15		K/W	

preliminary

Package TO-268AA (D3Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			70	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		150	°C
<b>Weight</b>				5		g
$F_C$	mounting force with clip		20		120	N

**Product Marking**

**Part number**

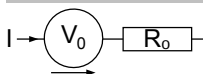
I = IGBT  
 X = XPT IGBT  
 A = Gen 1 / std  
 12 = Current Rating [A]  
 IF = Copack  
 1200 = Reverse Voltage [V]  
 TC = TO-268AA (D3Pak) (2)

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	IXA12IF1200TC	IXA12IF1200TC	Tube	30	508475

Similar Part	Package	Voltage class
IXA12IF1200HB	TO-247AD (3)	1200
IXA12IF1200PB	TO-220AB (3)	1200

**Equivalent Circuits for Simulation**

\* on die level

 $T_{VJ} = 150\text{ °C}$ 

 $V_{0\ max}$  threshold voltage

 $R_{0\ max}$  slope resistance \*

**IGBT**

1.1

153

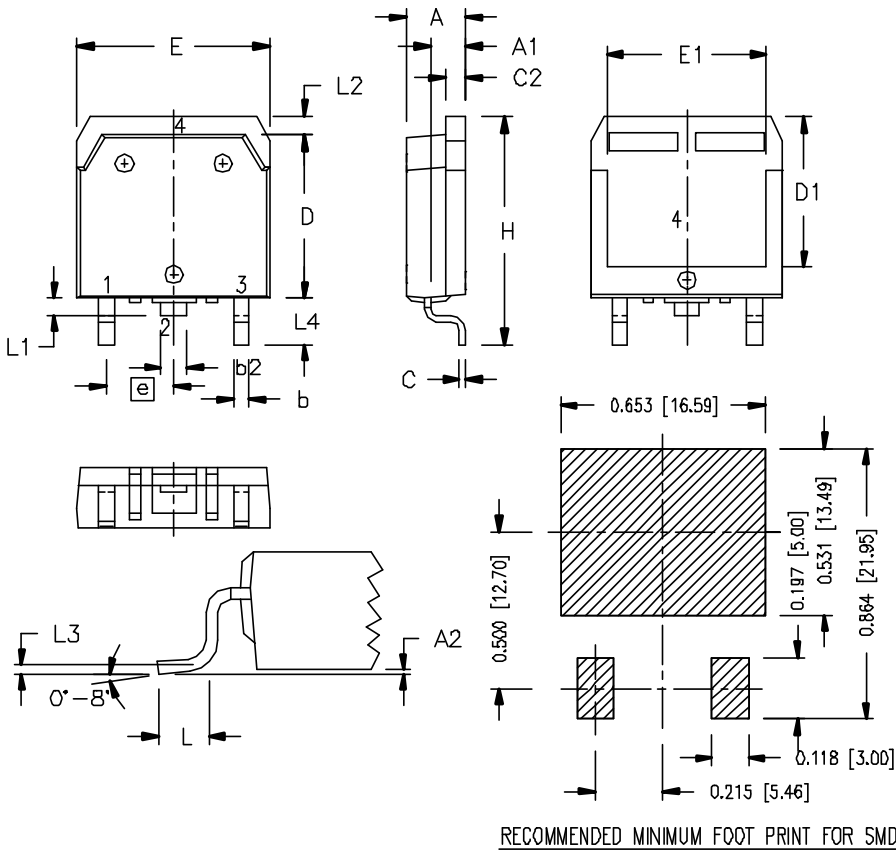
**Diode**

1.25

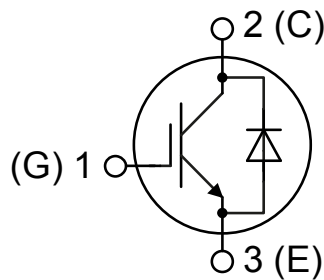
85

V

mΩ

**Outlines TO-268AA (D3Pak)**


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.90	5.10	0.193	0.201
A1	2.70	2.90	0.106	0.114
A2	0.02	0.25	0.001	0.100
b	1.15	1.45	0.045	0.057
b2	1.90	2.10	0.075	0.083
C	0.40	0.65	0.016	0.026
C2	1.45	1.60	0.057	0.063
D	13.80	14.00	0.543	0.551
D1	12.40	12.70	0.488	0.500
E	15.85	16.05	0.624	0.632
E1	13.30	13.60	0.524	0.535
e	5.45 BSC		0.215 BSC	
H	18.70	19.10	0.736	0.752
L	2.40	2.70	0.094	0.106
L1	1.20	1.40	0.047	0.055
L2	1.00	1.15	0.039	0.045
L3	0.25 BSC		0.100 BSC	
L4	3.80	4.10	0.150	0.161



## IGBT

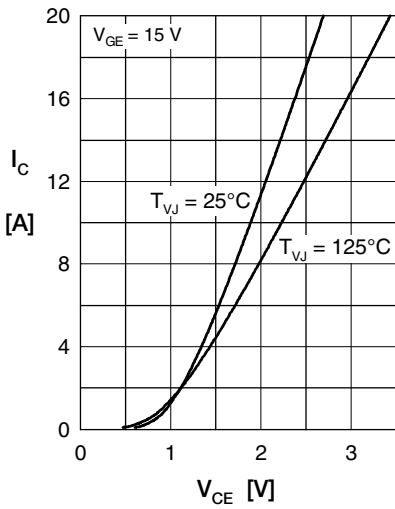


Fig. 1 Typ. output characteristics

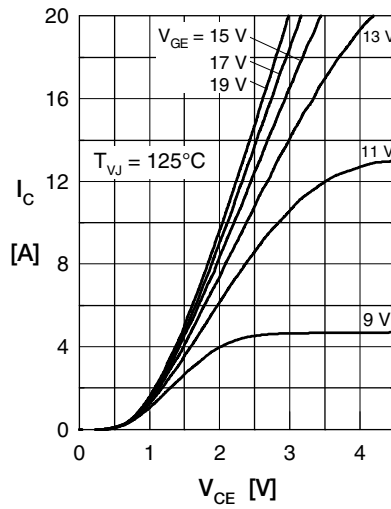


Fig. 2 Typ. output characteristics

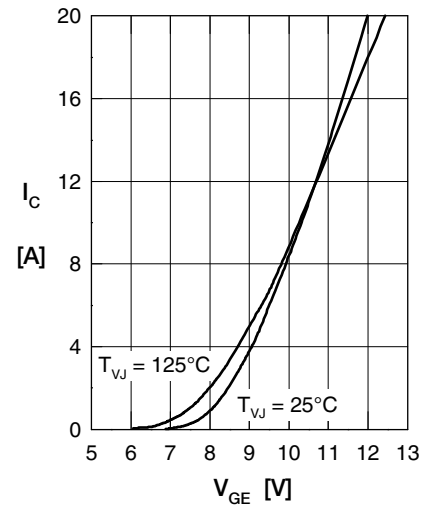


Fig. 3 Typ. transfer characteristics



Fig. 4 Typ. turn-on gate charge



Fig. 5 Typ. switching energy vs. collector current

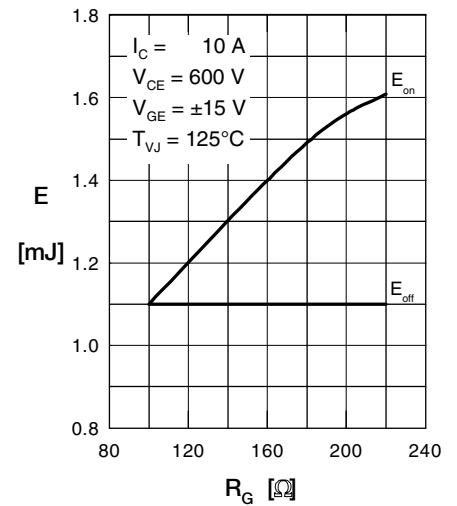


Fig. 6 Typ. switching energy vs. gate resistance

Fig. 7 Typ. transient thermal impedance junction to case

**Diode**

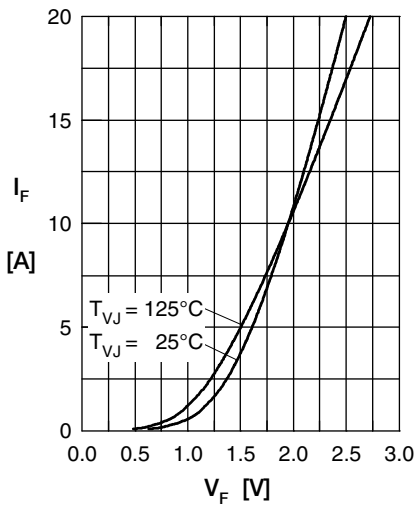


Fig. 1 Typ. forward current versus  $V_F$

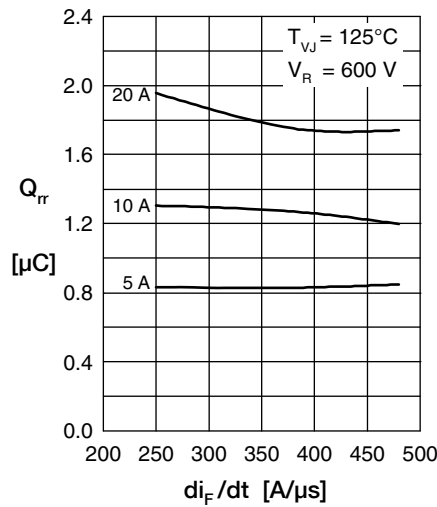


Fig. 2 Typical reverse recov. charge  $Q_{rr}$  versus  $di_F/dt$

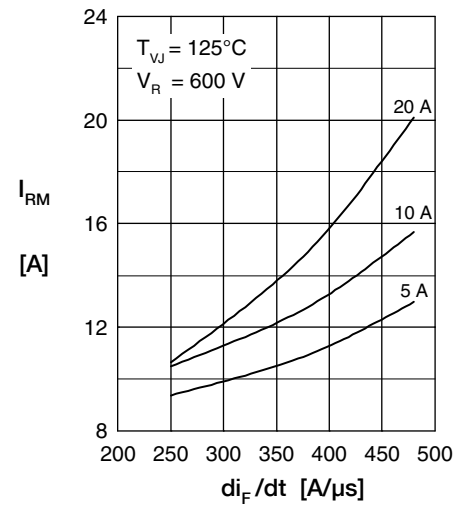


Fig. 3 Typ. peak reverse current  $I_{RM}$  versus  $di_F/dt$

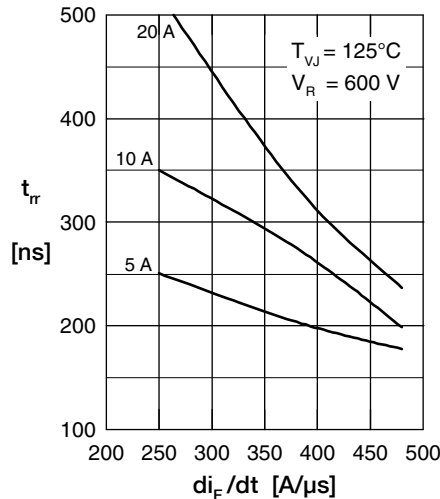


Fig. 4 Dynamic parameters  $Q_{rr}$ ,  $I_{RM}$  versus  $T_{VJ}$

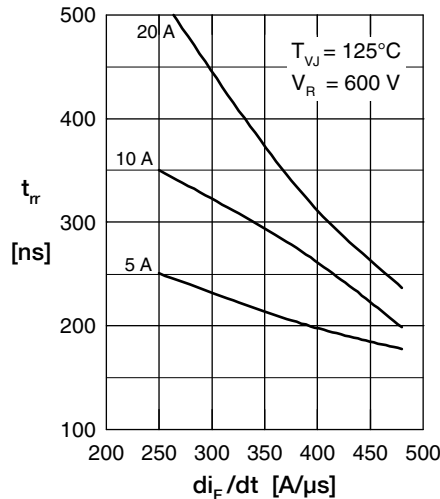


Fig. 5 Typ. recovery time  $t_{rr}$  versus  $di_F/dt$

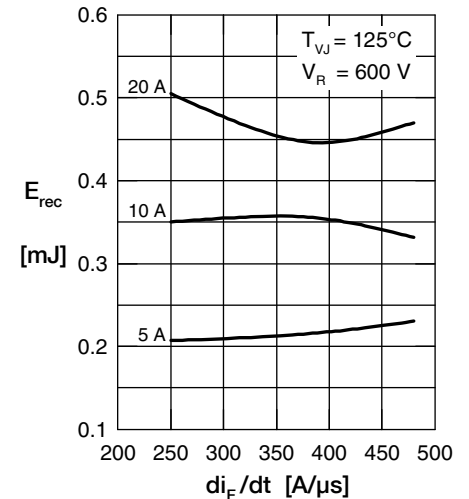


Fig. 6 Typ. recovery energy  $E_{rec}$  vs.  $di_F/dt$

Fig. 7 Typ. transient thermal impedance junction to case



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